Imaging impurities at quantum Hall edges in graphene: Dissipation and resistance rings

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Motivated by the recent experiment by Marguerite et al. [1] on imaging in graphene samples, we investigate theoretically the effect of impurities in the quantum Hall regime on the heat production and the electric resistance. The impurity-induced forward scattering in quantum Hall edges leads to enhanced energy transfer between electrons and phonons, which is most efficient when the impurity state is fine-tuned to a resonance by an applied tip voltage (resonant “supercollisions”). Edge reconstruction in graphene introduces pairs of counter-propagating channels. The backscattering between these channels leads to a finite longitudinal resistance $R_{xx}$, which is affected by local external potentials (of an impurity and of a scanning tip). Our analysis of the effect of a tip potential on the dissipation and resistance reveals peculiar spatial ring-shaped structures near an impurity, in consistency with experimental observations.

Introduction—Although the quantum Hall (QH) effect has been studied for decades, it continues to attract attention of the community for multiple reasons. To begin with, at the QH plateau, mobile quasiparticles are confined within the sample edges. Consequently, QH problems bridge two-dimensional (2D) and one-dimensional (1D) physics, with the latter allowing for exact description in terms of bosonization and other well-developed techniques [2–5]. The second reason is the chiral nature of edge excitations, which forbid backscattering in QH systems. The lack of backscattering further leads to the most distinguished feature of QH effect: the topologically protected quantized Hall conductance. This feature, which physically relates QH effect to other topology-related topics [6–12], is the major reason of the long-lasting interest on QH effect: in particular, multiple QH-involved complex structures have been proposed as possible hosts of quasiparticles with exotic statistics [8,13–16].

The absence of backscattering is commonly associated with the absence of energy dissipation in the topologically protected edge channels. However, strictly speaking, the vanishing of dissipation and the invariant resistance are only pertinent to “ideal” quantum Hall systems. On one hand, realistic graphene samples contain resonant impurities that, as we show below, may assist dissipating energy from chiral nonequilibrium electrons even by forward scattering, i.e., without affecting the electrical resistance. On the other hand, graphene is known for the edge reconstruction effect [17–23] which introduces pairs of counter-propagating non-topological edge channels. As a result, the quantization of the Hall conductance in sufficiently small samples may be broken by the contribution of these additional channels which is influenced by local defects or potentials that leads to backscattering between the counterpropagating modes. Although the transport in edges with counterpropagating modes has been considered for the fractional QH [4,24–27], it has not been substantially investigated in integer QH systems except for the most recent experiments [1]. In this Letter, we highlight and theoretically explain the two fascinating features observed in this experiment: the ring-shape structure of the measured thermal and resistance profiles as functions of the tip position through which a local potential is applied.

The system—We consider a sample which consists of a graphene layer encapsulated between two hexagonal Boron Nitride (h-BN) substrates [1]. The system is placed under a perpendicular quantizing magnetic field that confines extended electron states to the range of the order of the magnetic length $l_m = \sqrt{\hbar/eB}$ ($h = 1$ for brevity) at the edge of the sample. A metallic gate beneath the sample applies the backgate voltage $V_{BG}$ to globally control the charge density. A superconducting tip (“SQUID-on-tip” [28–30]) is placed above the top h-BN layer. The role of the tip is twofold: on one hand, it serves as an effective impurity characterized by the tip voltage which locally controls the electrical property of the sample; on the other hand, it measures the local temperature reflecting the energy dissipation rate [29,30].

We model the system by an effective single-particle Hamiltonian for electrons, which consists of five parts:

$$H = H_0(B) + V_{\text{conf}} + V_{\text{local}} + V_{\text{e-e}} + V_{\text{e-ph}}.$$  

Here, the first term

$$H_0(B) = \begin{bmatrix} (\vec{p} + e\vec{A}) \cdot \vec{\sigma} - V_{BG}\sigma_0 & 0 \\ 0 & (\vec{p}' + e\vec{A}) \cdot \vec{\sigma} - V_{BG}\sigma_0 \end{bmatrix}$$

describes the motion of graphene electrons under the backgate voltage in the presence of magnetic field, with $\vec{p}'$ the momentum operator and $\vec{\sigma}$ the Pauli matrix for the sublattice pseudospin. In what follows, we choose the $z$ axis to be directed along the magnetic field and the $x$ axis along the sample edge, and use the gauge $\vec{A} = (By, 0, 0)$. The density of states is written as a sum over Landau levels, as

$$\rho^{e/h}(E) = \sum_{N=0}^{\infty} \frac{g}{2m^*} \delta(E - \sqrt{N}\omega_c).$$
for electrons (−) and holes (+), where \(\sqrt{N} \omega_i\) is the energy of the \(N\)th graphene Landau level. The degeneracy factor \(g = 2\) if \(N = 0\) and \(g = 4\) otherwise. The second term in Eq. (1) describes the confinement that provides vanishing of the density at the graphene-vacuum boundary. Supplementing Eq. (1) by this term, one gets non-interacting electron wave functions \([33–37]\).

The third term in Eq. (1) describes local potentials applied by the tip and produced by impurity charges,

\[
V_{\text{local}} = V_{\text{tip}}(|\vec{r}_{\text{tip}} - \vec{r}|) + \sum_i V_{\text{imp}}(|\vec{r}_i - \vec{r}|), \tag{4}
\]

We model \(V_{\text{tip}}\) and \(V_{\text{imp}}\) as spatially localized potentials

\[
\begin{align*}
V_{\text{tip}}(|\vec{r} - \vec{r}_{\text{tip}}|) &= V_0 \exp(-|\vec{r} - \vec{r}_{\text{tip}}|^2/l_{\text{tip}}^2)
V_{\text{imp}}(|\vec{r} - \vec{r}_i|) &= V_i \exp(-|\vec{r} - \vec{r}_i|^2/l_{\text{imp}}^2),
\end{align*}
\tag{5}
\]

characterized by the lengths \(l_{\text{tip}}\) and \(l_{\text{imp}}\), respectively.

To take into account the effect of the interaction-induced edge reconstruction, we employ the Thomas-Fermi approximation where the interaction effects are encoded in the effective potential, the fourth term \(V_{\text{e-e}}\) in Eq. (1). For simplicity, we only include the Hartree potential, \(V_{\text{e-e}} \to V_{\text{H}}(\vec{r})\), where

\[
V_{\text{H}}(\vec{r}) = -\frac{e^2}{4\pi\mathcal{E}r} \int d\vec{r}' \left[\frac{n(\vec{r}')}{|\vec{r} - \vec{r}'|} - \frac{n(\vec{r})}{\sqrt{|\vec{r} - \vec{r}'|^2 + 4h^2}}\right]. \tag{6}
\]

Here \(\mathcal{E}\) is the system dielectric constant and \(h\) is the distance from the graphene sample to the metallic back gate.

The last term in Eq. (1) describes a phonon-induced potential for electrons. After the projection onto the 1D edge, this potential, written in terms of the phonon operators \(b_{\vec{q}}\), reads

\[
V_{\text{e-ph}} = g_0 \sum_{\vec{q}} F(\vec{q}) \sqrt{\omega_0(b_{\vec{q}} + b_{\vec{q}}^\dagger)} e^{i\vec{q}\cdot\vec{r}}. \tag{7}
\]

Here, \(g_0\) is the electron-phonon interaction strength, \(\omega_0 = s\mu\) the acoustic phonon dispersion with the sound velocity \(s\), and \(F(\vec{q})\) the form factor \([38]\)

\[
F(\vec{q}) = \int_0^\infty dy \sqrt{2} \sin(q_y y) \varphi_{\vec{k}+\vec{q}}(y) \varphi_{\vec{k}}(y), \tag{8}
\]

with \(\varphi_{\vec{k}}(y)\) the \(y\)-direction wave-function of electrons that decays exponentially within \(l_{\text{m}}\). Notice that in Eq. (8) the momentum conservation along the \(y\) direction has been relaxed by the recoiled phonon produced by the graphene lattice \([39]\). Because of the \(\sim \sin(q_y y)\) oscillation, strictly speaking, the expression of the form-factor depends on the ratio between the thermal momentum \(q_T \equiv k_B T_d/s\) and the inverse magnetic length \(l_{\text{m}}^{-1}\), where \(T_d\) is the electron temperature. For simplicity, we assume that \(q_T \gg l_{\text{m}}^{-1}\). In this case, \(\sin(q_y y)\) of Eq. (8) oscillates strongly so that \(F(\vec{q}) \approx C/(q_y l_{\text{m}})\), where \(C\) is a \(q_y\) independent prefactor. It is not difficult to generalize our analysis onto the other limit \(q_T \ll l_{\text{m}}^{-1}\); this does not change our main conclusions.

With the model introduced above, we study the effect of impurities and the tip potential on the resistivity and dissipation in a graphene sample in the quantum Hall regime. We focus on the ring-shape features of the two profiles as functions of the tip position. One of them is the thermal rings induced by the on-resonance impurities \([40]\). The other one is the ring-shape map of the longitudinal resistance \(R_{xx}\) \([41]\) showing the dependence of the four-point resistance on the tip position, which originates from the interplay between two local potentials, \(V_{\text{tip}}\) and \(V_{\text{imp}}\).

**Thermal rings**—As we show below, the thermal rings arise already for a single chiral channel, i.e., they are not related to the edge reconstruction. This is also consistent with experimental observations \([11]\). We thus study in this part of the paper the physically simplest situation where phonons are produced within a single chiral channel in the presence of a single impurity. Importantly, for the linearized edge dispersion, a weak impurity potential introduces only an energy-independent phase factor in the scattering states, which does not affect the electron-phonon matrix element. Therefore, we focus on resonant impurity scattering that gives rise to “resonant supercancellations”.

Physically, a resonant impurity can be considered as an effective quantum dot that contains discrete energy levels. A variation of the local potential near the edge can also introduce an “antidot” hosting a closed edge state around it. In both cases, the system can be modeled \([40]\) as a chiral 1D wire tunnel-coupled with a quantum dot:

\[
H_{\text{edge}} = H_{\text{edge}} + H_T + H_{\text{dot}}, \tag{9}
\]
where $H_{\text{edge}} = -i v \partial_x - \mu$ describes 1D chiral electrons on the edge ($v$ is the velocity, $\mu$ chemical potential) and the dot-edge tunneling term $H_T$ is characterized by the matrix element $t$ (assuming pointlike tunneling at $x = 0$, for simplicity). Further, we assume that the dot (described by $H_{\text{dot}}$) has only one state $\phi_d$ with energy $\epsilon_d$ and neglect the dot-edge Coulomb interaction.

Following Ref. [41], the electron wave-function in the presence of the dot is written as [43]:

$$
\psi_k = \psi_k^{(0)} + \frac{t}{\epsilon_k - \epsilon_d + i \Gamma} \left( \phi_d + \int \frac{dk'}{2\pi} \frac{t \psi_k^{(0)}}{\epsilon_k' - \epsilon_d + i \eta} \right),
$$

where $\psi_k^{(0)}$ is the unperturbed electronic plane wave, $\Gamma = |t|^2/(2\nu)$ is the level broadening [42], and $\eta$ is a positive infinitesimal. In Eq. (10), the first and second parts correspond to the free and the scattered state operators, respectively. Considering an infinite chiral spectrum $\epsilon_k = v k - \mu$, the integral over $k'$ in wave-function (10) is given by its residue $\epsilon_d = \epsilon_k$. Then the wave-function on the edge can be conveniently written in terms of the $k$-dependent phase shift of the plane wave at $x > 0$:

$$
\psi_k = \psi_k^{(0)} \exp \left[ -i \Theta(x) \arctan \frac{2(\epsilon_k - \epsilon_d)\Gamma}{(\epsilon_k - \epsilon_d)^2 + \Gamma^2} \right],
$$

where $\Theta(x)$ is the Heaviside theta-function.

The energy dissipation rate corresponds to the transitions between the initial ($i$) and final ($f$) states mediated by the electron-phonon interaction [44] [45], with the transition rate

$$
\Gamma_{i \rightarrow f} = \pi ||\langle f|V_{\text{e-ph}}|i\rangle||^2 \delta(E_i^\text{el} - E_f^\text{el} \pm E_{\text{ph}}).
$$

Here $E_i^\text{el}$ and $E_f^\text{el}$ are the electron energies of the initial and final states, respectively, $E_{\text{ph}}$ is the energy of the emitted/absorbed phonon, and the bar denotes the angle average over thermal phonon states characterized by the lattice temperature $T_{\text{lattice}}$. Based on Eq. (10), the phonon emission contains two parts. The first part is the phonon-assisted scattering between two free-electron states without any impurity [39],

$$
P_0 = \frac{\hbar^2}{12} s \frac{C^2}{v} k_B^2 (T_{\text{edge}}^2 - T_{\text{lattice}}^2).
$$

The second part refers to the impurity-assisted scattering, which involves one or two scattered state operators as the initial or (and) final states. For simplicity, we consider the most interesting regime where $\Gamma, \epsilon_d \ll k_B T_{\text{edge}}$. In this regime, the impurity-induced energy dissipation rate becomes

$$
P_1 = \frac{\sqrt{2} \hbar^2}{6} \frac{s}{v} \frac{C^2}{k_B^2} \frac{\Gamma^2}{T_{\text{edge}}^2 - T_{\text{lattice}}^2} \frac{\Gamma^2}{2 + \epsilon_d^2}.
$$

Clearly, Eq. (14) has a resonant feature. More specifically, it reaches its maximum when $\epsilon_d \ll \Gamma$, where the impurity is tuned on-resonance, and decays away from the resonance in a Lorentzian manner. Since the on-resonance value of Eq. (14) is of the same order as the impurity-free dissipation rate Eq. (15), the resonance feature is detectable with thermal-imaging techniques.

Experimentally, the dissipated energy is transferred from the electronic system to phonons and measured by a local thermometer. Since the energy $\epsilon_d$ is tunable through the tip voltage as a function of the tip-impurity distance, the tip positions at which the temperature peak is observed form a ring pattern, as indicated by Fig. 1(a). This impurity-induced phonon emission is the 1D version of a resonant supercollision [45] [46]. Considering a scattering-induced phase shift $\theta(k)$, Eq. (11), for a particle with momentum $k$, in addition to the momentum-conservation term, the scattering matrix between the initial ($k_i$) and final ($k_f$) states $(k_f|x|\exp(iq_xx)|k_i)$ produces the term $\propto \cos[\theta(k_i) - \theta(k_f)] - 1$. This term vanishes when the phases are $k$-independent, thus explaining no effect of weak potential scatterers in 1D chiral edges, which should be contrasted with supercollisions induced by non-resonant impurities in 2D graphene samples [44].

Impurity-induced rings in $R_{xx}$ maps—As is well known, in ideal QH systems, the Hall conductance $\nu e^2/h$ only depends on the bulk filling factor $\nu$ and becomes protected against any local defect or potential. However, this is not the case in graphene where peculiar electrostatic effects lead to appearance of additional counter-propagating channels in the reconstructed edge [17]. In this case, when a potential that locally depletes the quasiparticle density is applied between two non-topological channels through the tip, the backscattering between them increases. Intuitively, this backscattering strongly enhances the local equilibration between different channels, leading to a sharp voltage drop in the affected area. Consequently, if two voltage probes are placed at different sides of the tip, the measured voltage drop $V_{xx}$ and the related $R_{xx}$ will increase. The detailed verification of the argument involves equations that dynamically calculate the evolution of chemical potentials [43].

The problem becomes more involved when both the impurity charge potential and the tip voltage coexist. More specifically, when $V_{BG} < 0$, the graphene bulk is tuned beneath the Dirac point. The impurity charge potential thus accumulates quasi-particles, and competes against the depleting effect of the tip voltage, as shown in Fig. 2.

To study the competing effect, we find the quasiparticle potential and density profiles iteratively with Eqs. (5)-(9). Within the Thomas-Fermi approximation, all quasiparticle interactions are included into the effective single-particle potential $V(\vec{r})$ used to calculate the charge density $n(\vec{r}) = n_e(\vec{r}) + n_h(\vec{r})$, where

$$
n_e(\vec{r}) = -\Theta(x) \int_{V(\vec{r})}^{\infty} \rho^e(E - V(\vec{r})) f_F^e(E, E_F) dE,
$$

$$
n_h(\vec{r}) = \Theta(x) \int_{-\infty}^{V(\vec{r})} \rho^h(E - V(\vec{r})) f_F^h(E, E_F) dE
$$

are the electron and hole densities [38], respectively, with $f_F^{e/h}(E, E_F) = 1/\{\exp(\pm (E - E_F)/T) + 1\}$ the quasiparticle
FIG. 2. The effect of the quasiparticle-depleting tip voltage (green) when it is applied on a reconstructed edge consisting of the right moving chiral (red) channel and two left moving (blue) ones: (a) in the area that is not affected by the impurity (red dot) charge potential; (b) near the inner non-topological channel; (c) in the area strongly influenced by the impurity potential; and (d) next to the physical boundary (the black line). In all cases but (c), either the non-topological channel is broken in the middle (a), or the distance between the inner channels strongly decreases [(b) and (d)], thus leading to a manifest $R_{xx}$ enhancement. These cases correspond to potentials plotted in Figs. 3(c)-(f), respectively.

Fermi distribution function.

We present the hole density profiles obtained numerically from these equations in Fig. 3. Figure 3(a) shows the hole density without tip or impurity. As a comparison, in Fig. 3(b), holes gather around the impurity placed at $\vec{r} = (125, 0)$, as expected. The density profile after the application of the tip voltage near the impurity is shown in Figs. 3(c)-(f), where the result apparently depends on the tip position. More specifically, if the tip is applied in the area heavily influenced by the impurity charge potential [Fig. 3(e)], the distance between the non-topological channels is almost intact. In contrast to that, in other cases, either the non-topological channels are destroyed [Figs. 3(c)], or their inter-channel distance greatly decreases [Figs. 3(d) and 3(f)] because of the tip voltage. In the latter cases, the backscattering manifestly increases, leading to a stronger $R_{xx}$ enhancement compared to that of the former one as indicated by Fig. 3(g).

Consequently, its influence on $R_{xx}$ is weaker, when the tip voltage is suppressed by the impurity charge potential. A ring-shape $R_{xx}$ enhancement is thus expected, as shown schematically in Fig. 1(b). Note that the $R_{xx}$ rings are physically distinct from the thermal ones. Briefly, the thermal rings only require the existence of a single QH channel and resonant impurities. In contrast to that, the $R_{xx}$ rings require both edge reconstruction effect and the competition between two opposite local potentials.

Summary—We have reported the two non-trivial impurity-induced features of a graphene sample in the quantum Hall regime: (i) the thermal rings where the energy emission rate is maximized through supercollision at on-resonance quantum dots and (ii) the resistance rings arising from the competition between two opposite local potentials by boundary impurity and a local tip.

The energy dissipation rate is locally enhanced through the forward scattering of QH quasiparticles at resonant impuri-
ties. This enhancement, which is related to the momentum-dependent phase shift produced during forward scatterings, leads to a finite impurity-induced energy dissipation rate even in a single chiral channel, thus explaining the appearance of thermal ("entropy") rings observed in a very recent experiment [1].

Further, we have studied the effect of local potentials in the graphene sample where counter-propagating channels are introduced by the edge reconstruction effect and the impurity-induced backscattering gives rise to equilibration between them. Here, we find that the tip voltage that locally depletes quasiparticles may increase the Hall resistance. This resistance enhancement, however, is suppressed by the presence of an impurity local potential that accumulates particles. Through numerical verification, we further obtain that the competition between these two physically distinct local potentials gives rise to the formation of ring-shape patterns in the $R_{xx}$ map as a function of the tip position, in agreement with the experimental data [1].

To summarize, both dissipation and resistance can be induced by the existence of impurities at the boundary of a graphene sample in the quantum Hall regime. These results, especially the impurity-induced dissipation, prove the importance of edge impurities in integer QH systems, which has not been sufficiently appreciated previously.

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